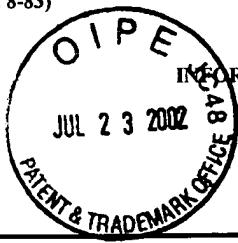


#18

Form PTO-1449 (Rev. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. <b>RTN2-047PUS</b>	APPLICATION NO. <b>09/504,660</b>
INFORMATION DISCLOSURE CITATION Page 1 of 1		APPLICANT(S) <b>William E. Hoke et al.</b>	
		FILING DATE <b>February 14, 2000</b>	GROUP <b>2811</b>



## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE*
nm		5	1	4	0	3	8	6	08/18/1992	Huang et al.			
im		5	2	8	5	0	8	7	02/08/1994	Narita et al.			
nm		5	4	3	6	4	7	0	07/25/1995	Nakajima			
bn		5	5	0	4	3	5	3	04/02/1996	Kuzuhara			
bnn		5	5	5	0	3	8	8	08/27/1996	Haruyama			
bnn		5	5	9	6	2	1	1	01/21/1997	Onda et al.			
bnn		5	6	4	1	9	7	7	06/24/1997	Kanamori			
bnn		5	8	1	1	8	4	3	09/22/1998	Yamamoto et al.			
nm		6	1	4	4	0	4	8	11/07/2000	Suemitsu et al.			
nr		6	1	4	4	0	4	9	11/07/2000	Onda			
nr		6	2	5	8	6	3	9	07/10/2001	Rohdin et al.			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	Country	Name	CLASS	SUBCLASS	TRANSLATION	
								YES	NO
nr		JP7193224 (ABSTRACT)	07/28/1995	Japan					

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nr	P. Ho et al; "Extremely High Gain, Low Noise InAl/As/InGaAs HEMTs Grown By Molecular Beam Epitaxy"; IEEE; 1998; pp. 184-186.
nr	Tom P.E. Broekaert et al.; "AlAs Etch-Stop Layers for InGaAlAs/InP Heterostructure Devices and Circuits"; IEEE; March 1992; Vol. 39, No. 3; pp. 533-536.
Examiner	<i>Kwak</i> Date Considered: <i>9-11-02</i>

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and considered. Include copy of this form with next communication to applicant.

(702143)

*Donghee Kang*